40V N-Channel Enhancement Mode MOSFET

MAIN CHARACTERISTICS

I_D	140A
V_{DSS}	40V
R_{DSON}-typ(@V_{GS}=10V)	2.7mΩ(Typ:

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	**BV_{DSS}**	40	-	-	**V**
Gate Body Leakage Current	V_{GS}=±20V, V_{DS}=0V	**I_{GSS}**	-	-	±100	**nA**
Drain-Source Leakage Current	V_{DS} = 40 V, V_{GS} = 0 V	**I_{DSS}**	-	-	1	**μA**
Gate Threshold Voltage	V_{DS}= V_{GS}, I_D=250μA	**$V_{GS(th)}$**				

Ratings and Characteristic Curves

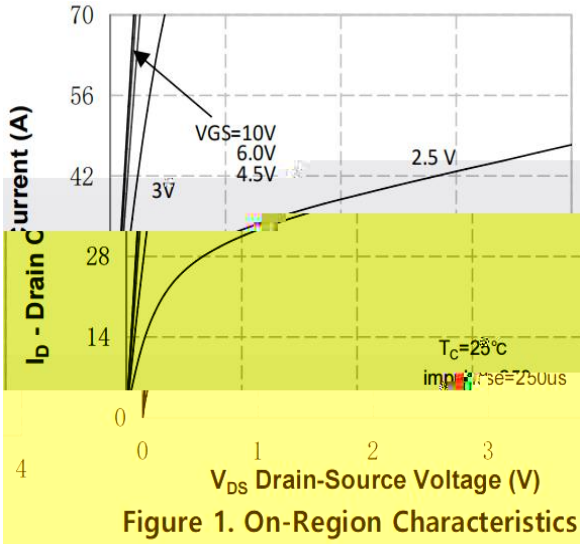


Figure 1. On-Region Characteristics

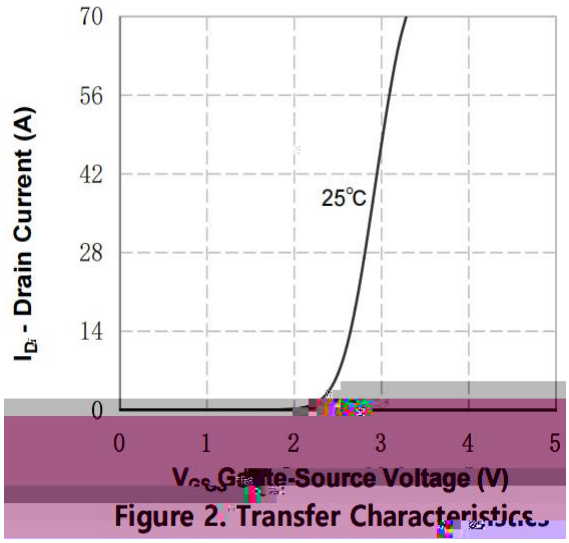
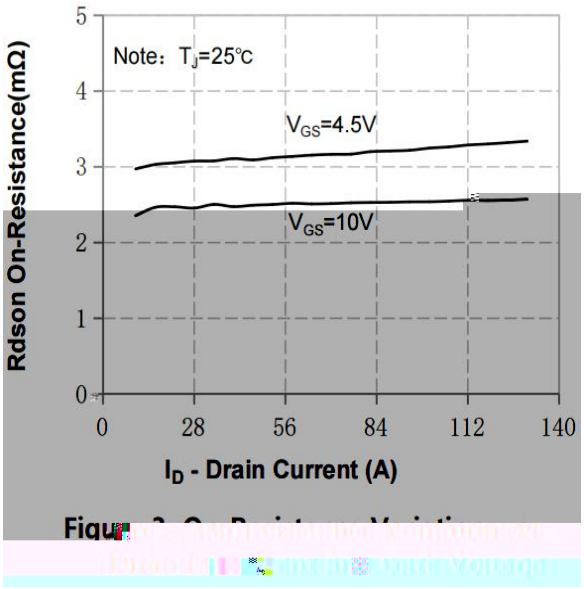
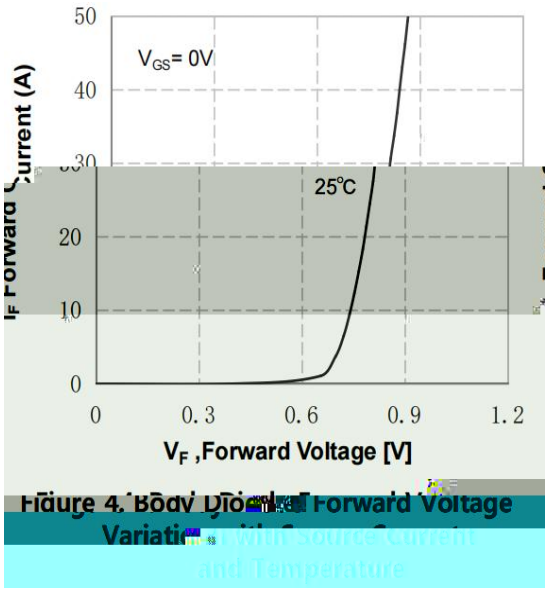
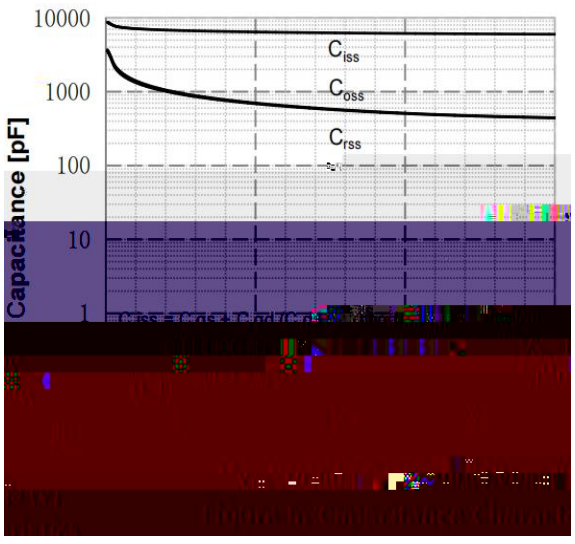


Figure 2. Transfer Characteristics







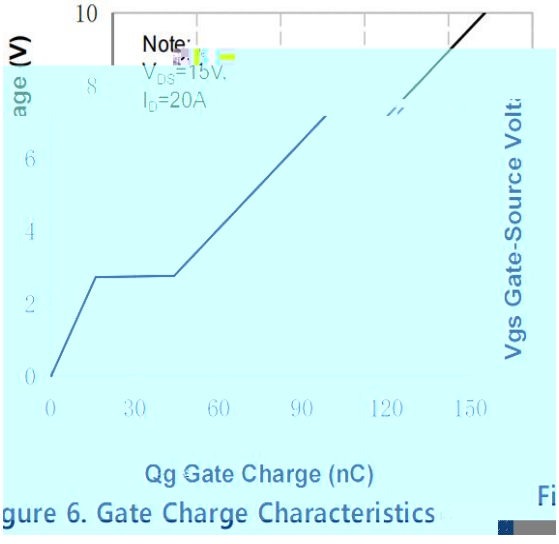


Figure 6. Gate Charge Characteristics

Ratings and Characteristic Curves

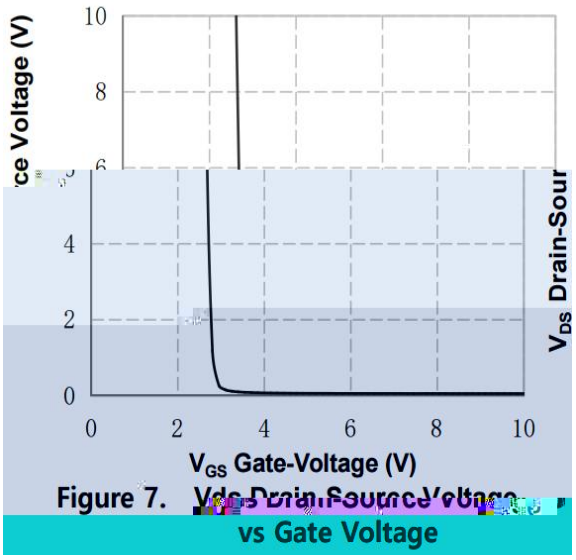


Figure 7. V_{DS} Drain-Source Voltage vs Gate Voltage

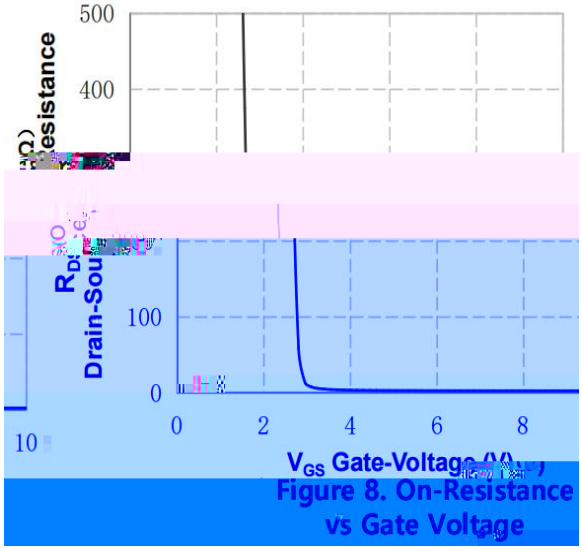
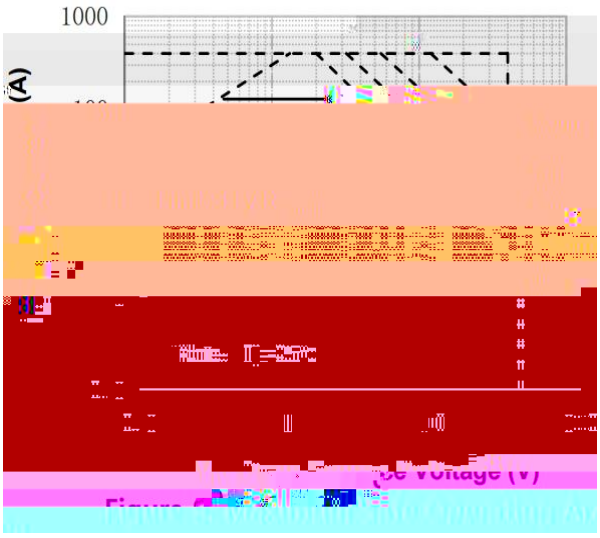
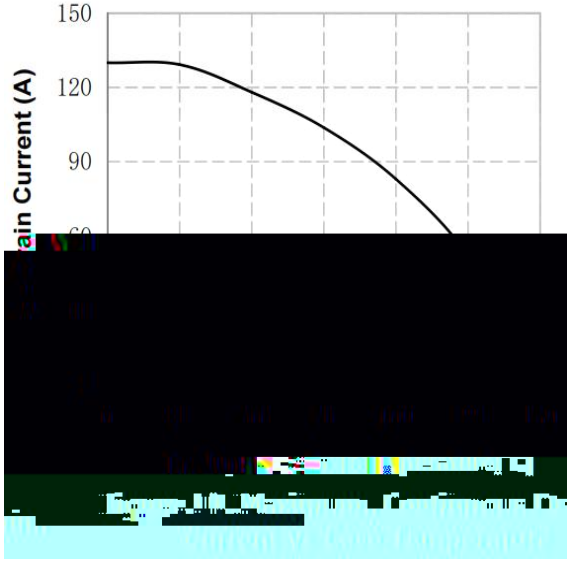
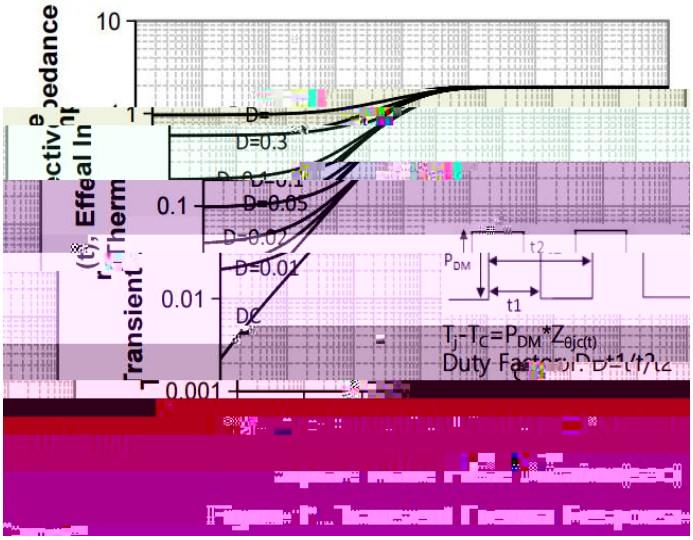


Figure 8. On-Resistance vs Gate Voltage







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